

GT07N65 Series

N-Channel Power Field Effect Transistor

Description

This high voltage MOSFET uses an advanced termination scheme to provide enhanced voltage-blocking capability without degrading performance over time. In addition, this advanced MOSFET is designed to withstand high energy in avalanche and commutation modes. The new energy efficient design also offers a drain-to-source diode with a fast recovery time. Designed for high voltage, high speed switching applications in power supplies, converters and PWM motor controls, these devices are particularly well suited for bridge circuits where diode speed and commutating safe operating areas are critical and offer additional and safety margin against unexpected voltage transients.

Features

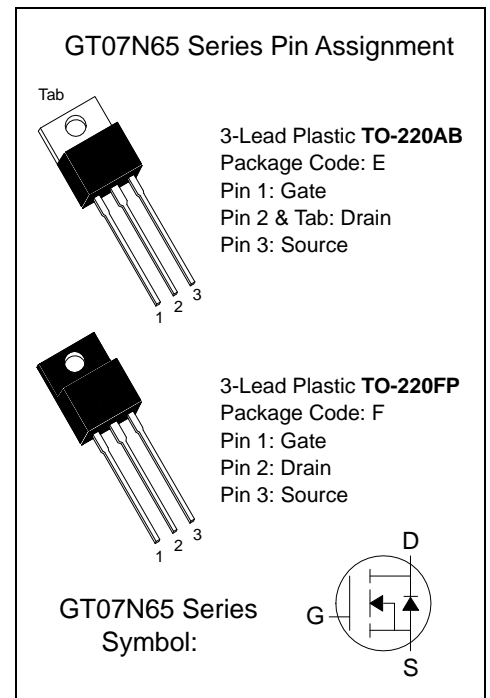
- Robust High Voltage Termination
- Avalanche Energy Specified
- Source-to-Drain Diode Recovery Time Comparable to a Discrete Fast Recovery Diode
- Diode is Characterized for Use in Bridge Circuits
- IDSS and $V_{DS(on)}$ Specified at Elevated Temperature

Absolute Maximum Ratings

Symbol	Parameter	Value	Units
V_{DS}	Drain-Source Voltage	650	V
I_D	Drain to Current (Continuous)	7	A
I_{DM}	Drain to Current (Pulsed)	28	A
V_{GS}	Gate-to-Source Voltage (Continue)	± 30	V
P_D	Total Power Dissipation ($T_C=25^\circ\text{C}$)		
	GT07N65E (TO-220AB)	120	W
	GT07N65F (TO-220FP)	48	W
	Derate above 25°C		
	GT07N65E (TO-220AB)	1.18	W/ $^\circ\text{C}$
	GT07N65F (TO-220FP)	0.38	W/ $^\circ\text{C}$
T_j	Operating Temperature Range	-55 to 150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
E_{AS}	Single Pulse Drain-to-Source Avalanche Energy- $T_j=25^\circ\text{C}$ ($V_{DD}=50\text{V}$, $V_{GS}=10\text{V}$, $I_L=7\text{A}$, $L=10\text{mH}$, $R_G=25\Omega$)	530	mJ
T_L	Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 10 seconds	260	$^\circ\text{C}$

Note: 1. $V_{DD}=50\text{V}$, $I_D=7\text{A}$

2. Pulse Width and frequency is limited by $T_{j(max)}$ and thermal response



Thermal Characteristics

Symbol	Parameter	Value		Units
R _{θJC}	Thermal Resistance Junction to Case Max.	TO-220AB	1.02	
		TO-220FP	3.3	
R _{θJA}	Thermal Resistance Junction to Ambient Max.	62		°C/W

Electrical Characteristics (T_J=25°C, unless otherwise specified)

Symbol	Characteristic	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-Source Breakdown Voltage (V _{GS} =0V, I _D =250uA)	650	-	-	V
I _{DSS}	Drain-Source Leakage Current (V _{DS} =650V, V _{GS} =0V)	-	-	1	uA
	Drain-Source Leakage Current (V _{DS} =650V, V _{GS} =0V, T _J =125°C)	-	-	50	uA
I _{GSSF}	Gate-Source Leakage Current-Forward (V _{gsf} =30V, V _{DS} =0V)	-	-	100	nA
I _{GSSR}	Gate-Source Leakage Current-Reverse (V _{gsr} =-30V, V _{DS} =0V)	-	-	-100	nA
V _{GS(th)}	Gate Threshold Voltage (V _{DS} =V _{GS} , I _D =250uA)	2	3	4	V
R _{DS(on)}	Static Drain-Source On-Resistance (V _{GS} =10V, I _D =3.5A)*	-	1	1.2	Ω
g _{FS}	Forward Transconductance (V _{DS} =15V, I _D =3.5A)*	2	-	-	S
C _{iss}	Input Capacitance	-	1095	-	pF
C _{oss}	Output Capacitance	-	95	-	
C _{rss}	Reverse Transfer Capacitance	-	3	-	
t _{d(on)}	Turn-on Delay Time	-	39	-	ns
t _r	Rise Time	-	29	-	
t _{d(off)}	Turn-off Delay Time	-	249	-	
t _f	Fall Time	-	37	-	
Q _g	Total Gate Charge	-	27	38	nC
Q _{gs}	Gate-Source Charge	-	5.1	-	
Q _{gd}	Gate-Drain Charge	-	8.5	-	

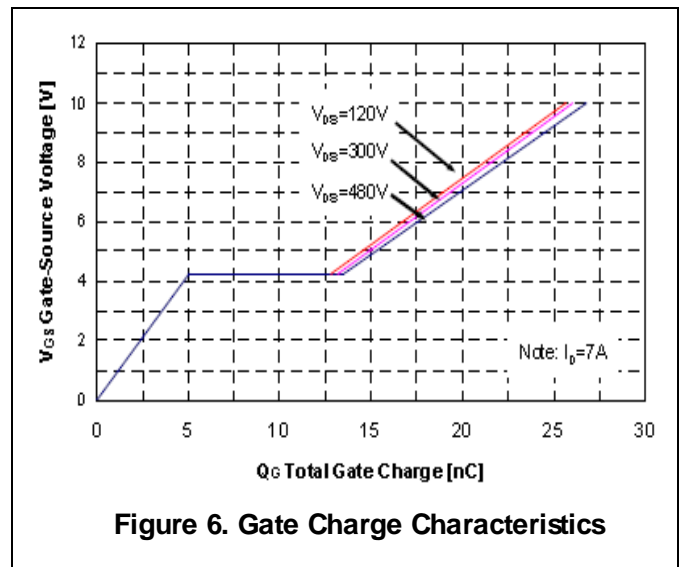
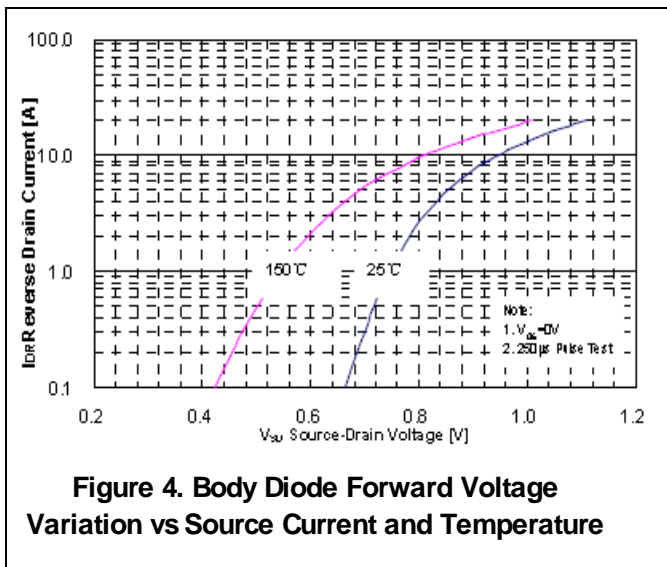
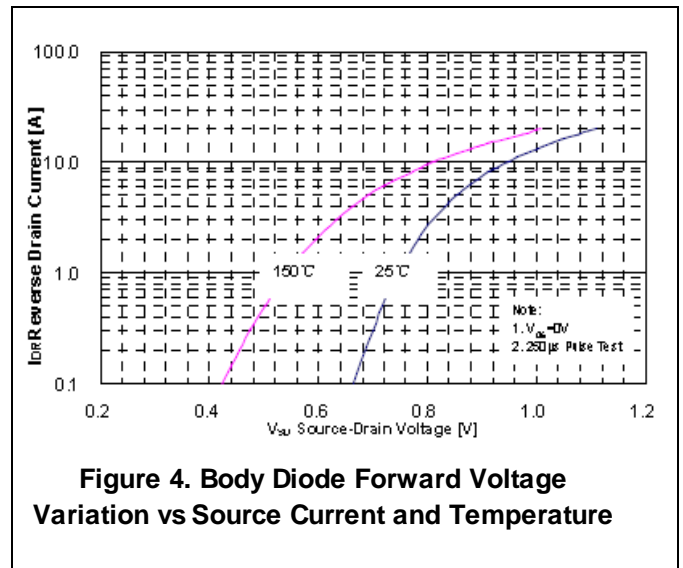
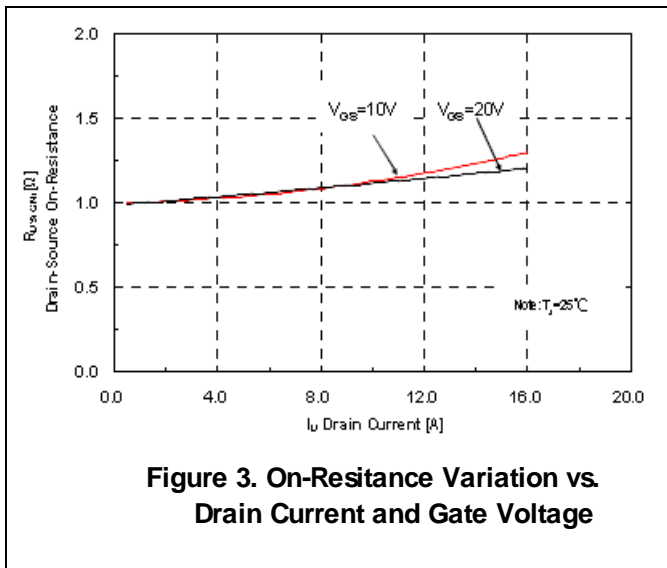
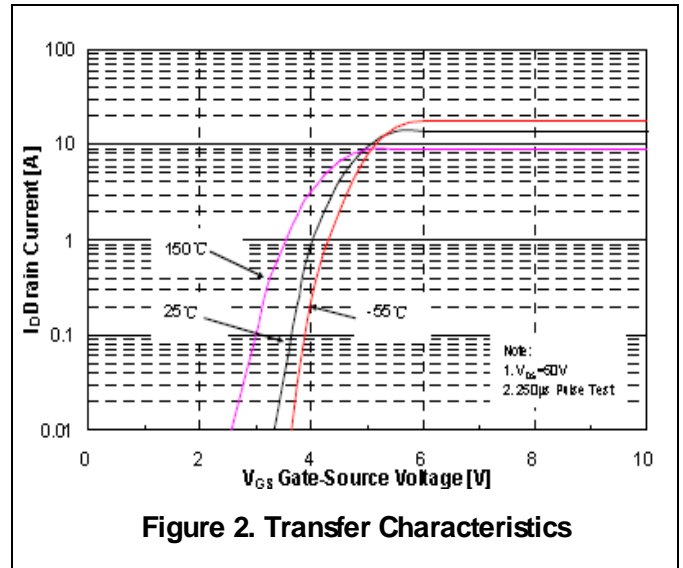
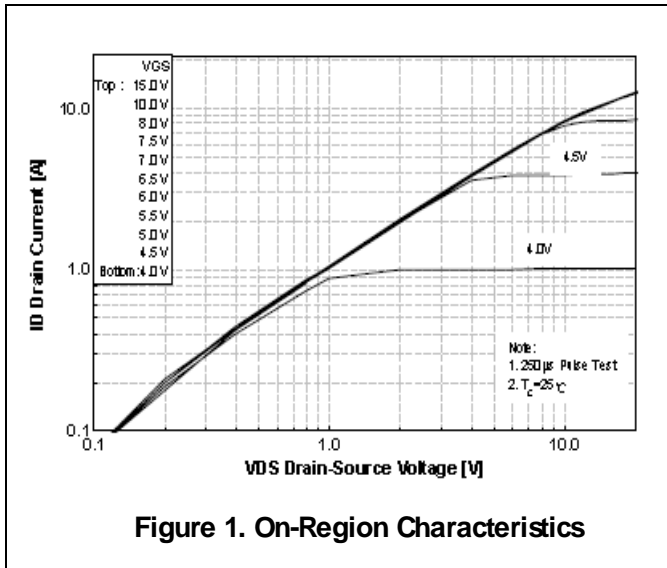
*: Pulse Test: Pulse Width ≤300us, Duty Cycle≤2%

Source-Drain Diode

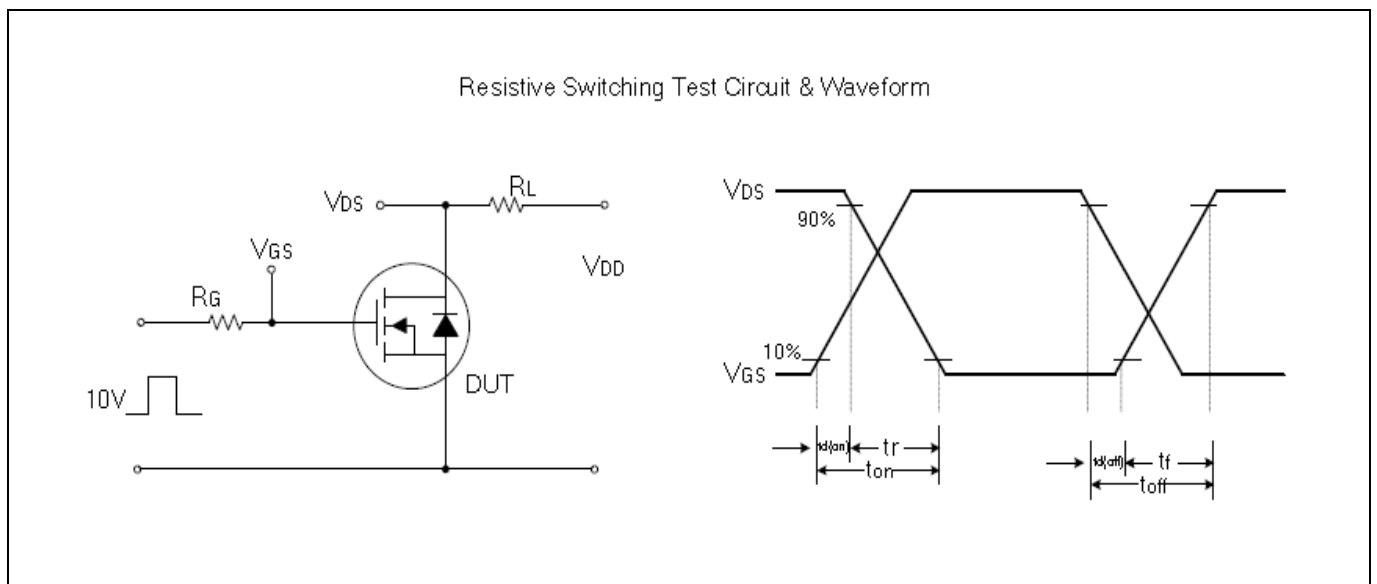
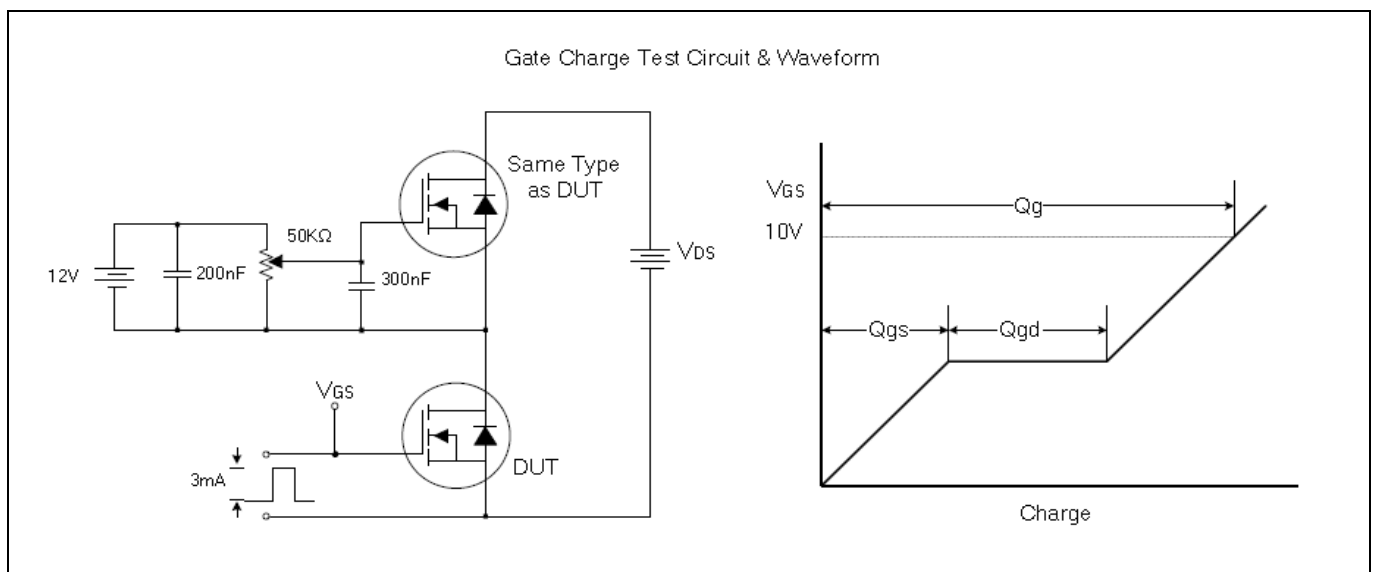
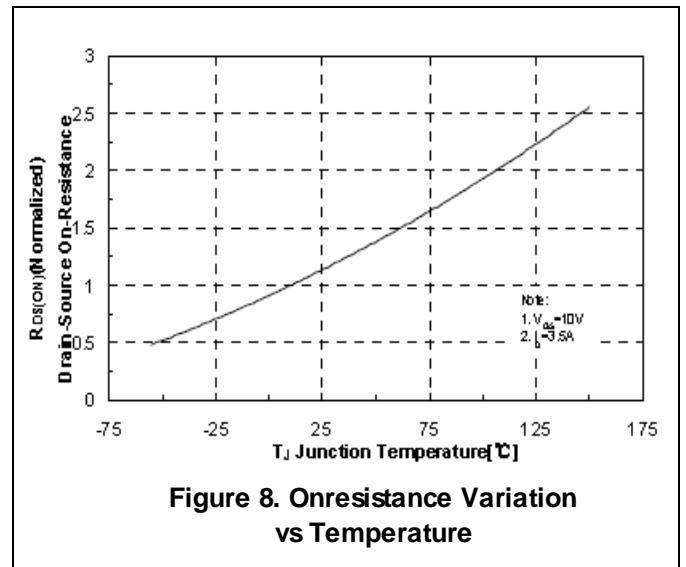
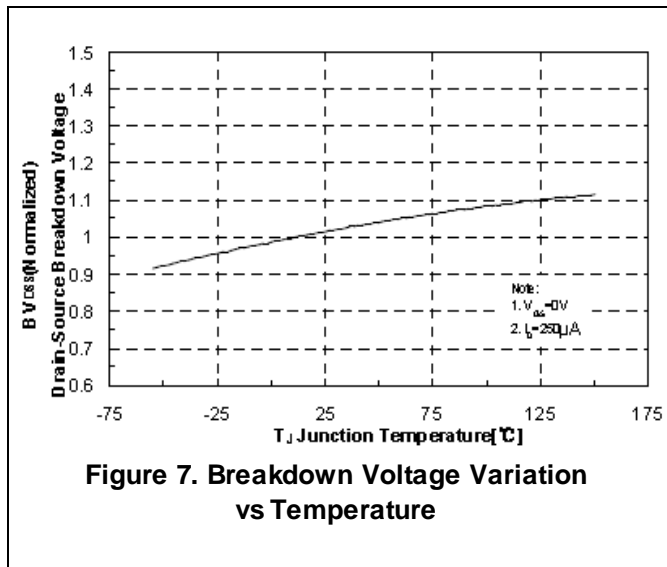
Symbol	Characteristic	Min.	Typ.	Max.	Units
V _{SD}	Forward On Voltage(1)	-	-	1.4	V
t _{rr}	Reverse Recovery Time	-	365	-	ns
Q _{rr}	Reverse Recovery Charge	-	3.5	-	ns

**: Negligible, Dominated by circuit inductance

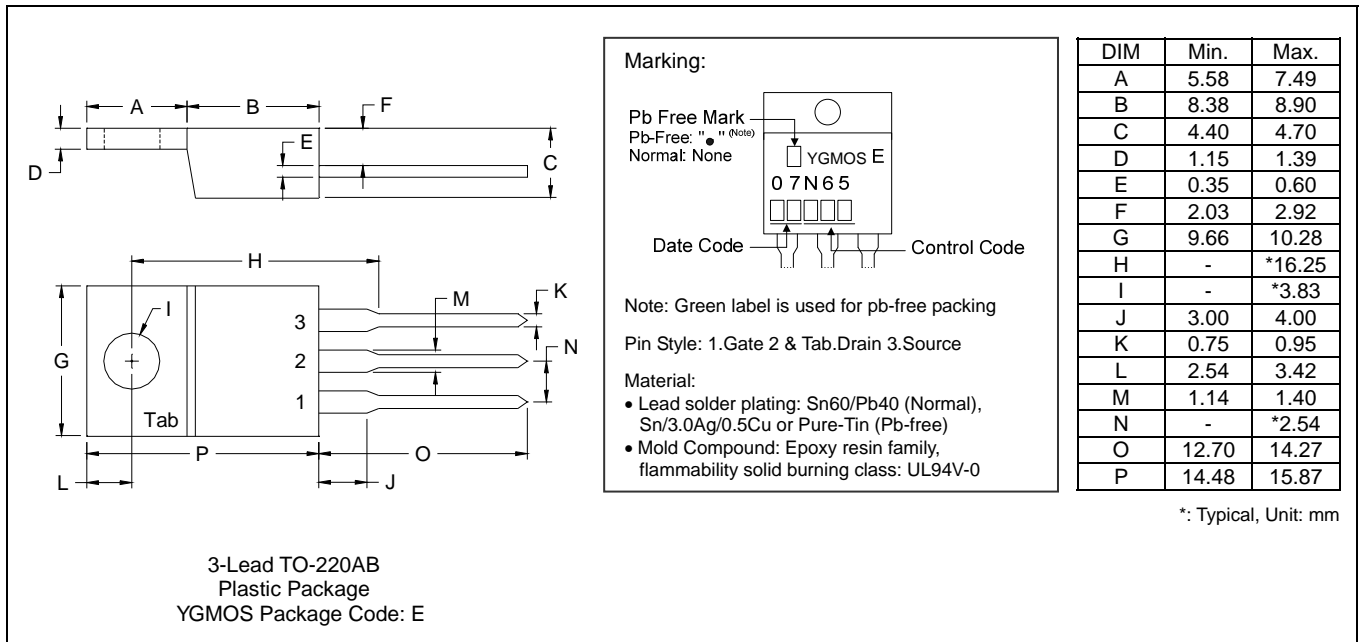
Characteristics Curve



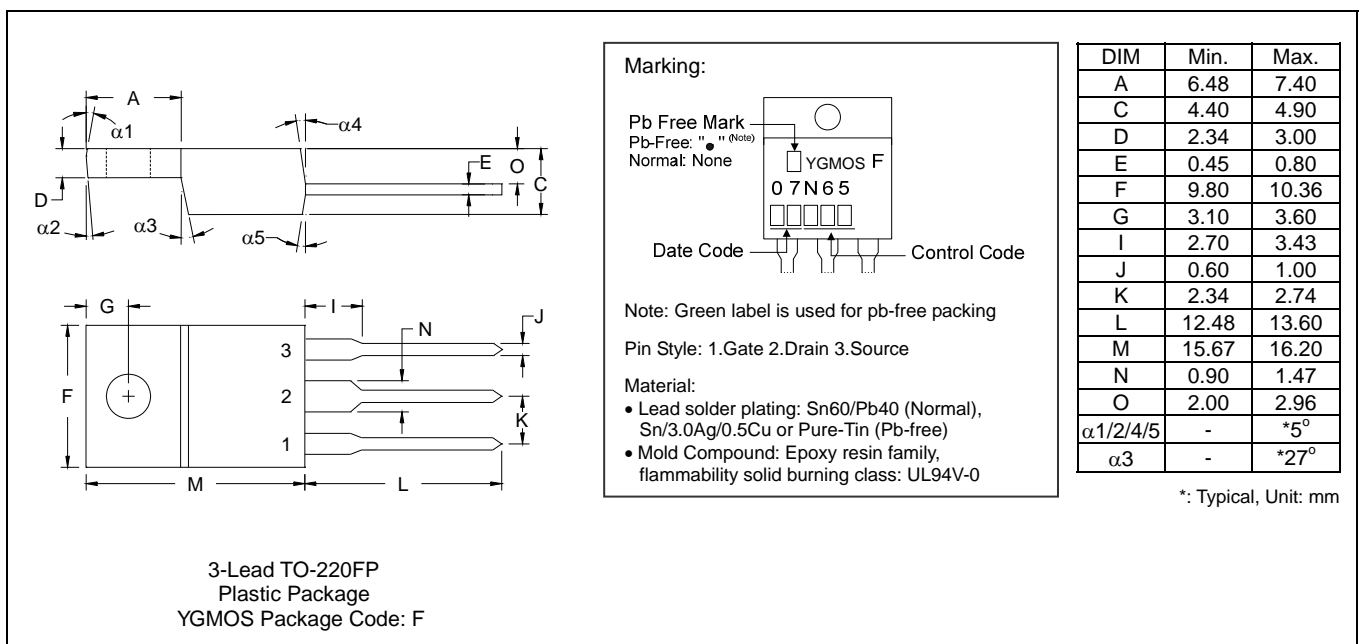
Characteristics Curve



TO-220AB Dimension

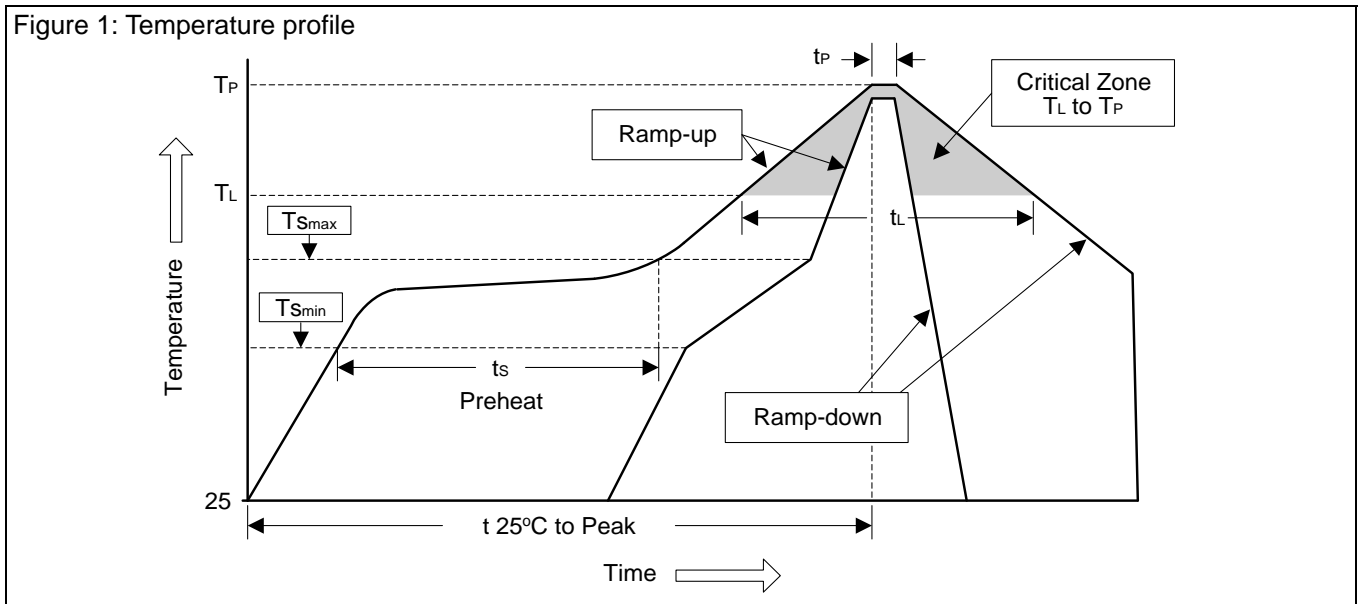


TO-220FP Dimension



Soldering Methods for YGMOS's Products

1. Storage environment: Temperature=10°C~35°C Humidity=65%±15%
2. Reflow soldering of surface-mount devices



Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate (T _L to T _P)	<3°C/sec	<3°C/sec
Preheat		
- Temperature Min (T _{Smin})	100°C	150°C
- Temperature Max (T _{Smax})	150°C	200°C
- Time (min to max) (t _s)	60~120 sec	60~180 sec
T _{Smax} to T _L		
- Ramp-up Rate	<3°C/sec	<3°C/sec
Time maintained above:		
- Temperature (T _L)	183°C	217°C
- Time (t _L)	60~150 sec	60~150 sec
Peak Temperature (T _P)	240°C +0/-5°C	260°C +0/-5°C
Time within 5°C of actual Peak Temperature (t _P)	10~30 sec	20~40 sec
Ramp-down Rate	<6°C/sec	<6°C/sec
Time 25°C to Peak Temperature	<6 minutes	<8 minutes

3. Flow (wave) soldering (solder dipping)

Products	Peak temperature	Dipping time
Pb devices.	245°C ±5°C	10sec ±1sec
Pb-Free devices.	260°C ±5°C	10sec ±1sec